查询CD40174供应商



Data sheet acquired from Harris Semiconductor SCHS104

CMOS Hex 'D'-Type Flip-Flop

High-Voltage Types (20-Volt Rating)

CD40174B consists of six identical 'D'-type flip-flops having independent DATA inputs. The CLOCK and CLEAR inputs are common to all six units. Data is transferred to the Q outputs on the positive-going transition of the clock pulse. All six flip-flops are simultaneously reset by a low level on the CLEAR input.

The CD40174B types are supplied in 16lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

DC SUPPLY-VOLTAGE RANGE, (VDD)

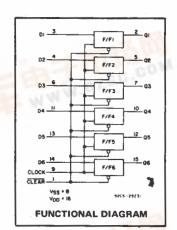
Voltages referenced to VSS Terminal) ...

LEAD TEMPERATURE (DURING SOLDERING):

Features:

- = 5-V, 10-V, and 15-V parametric rating
- Standardized symmetrical output characteristics
- = 100% tested for quiescent current at 20 V
- Maximum input current of 1 µA at 18 V over full peckage-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package-temperature range): 1 V at V_{DD} = 5 V
 - 2 V at VDD = 10 V
 - 2.5 V at VDD = 15 V

Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"



Applications:

捷多邦,专业PCB打样工厂,24小时加急出货

CD40174B Types

- Shift Registers
- Buffer/Storage Registers
- Pattern Generators

TRUTH TABLE FOR 1 OF 6 FLIP-FLOPS

	INPUTS	OUTPUT		
CLOCK	DATA	CLEAR	Q	
~	0	1	0	
	1	1	1	
~	×	1	NC	
X	×	0	0	

^{1 =} High Level X = Don't Care 0 = Low Level

NC = No Change

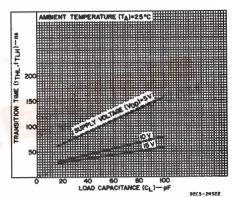
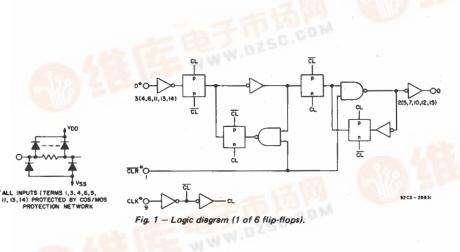
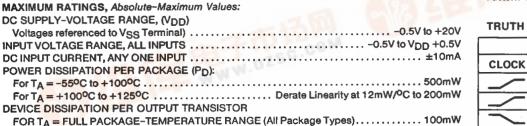


Fig. 2- Typical transition time as a function of load capacitance.



At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max +265°C

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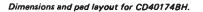


CD40174B Types

RECOMMENDED OPERATING CONDITIONS at $T_A = 25^{\circ}C$, Except as Noted. For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

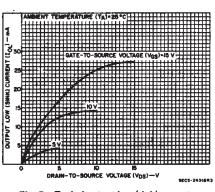
CHARACTERISTIC	VDD	LIN	UNITS	
	(V)	Min.	Max.	1
Supply-Voltage Range (For T _A = Full Package-	· ·			
Temperature Range)	-	3	18	v
	5	40	-	
Data Setup Time, t _{SU}	10	20	-	ns
	15	10		
	5	80	-	
Data Hold Time, t _H	10	40	-	ns
	15	30	-	
	5	-	3.5	
Clock Input Frequency, fCL	10	dc	6	MHz
	15		8	
	5	- 1	15	
Clock Input Rise or Fall Time, trCL, trCL	10	. –	15	μs
	15	-	15	
	5	130	-	
Clock Input Pulse Width, tWL, tWH	10	60	3 18 0 0	ns
	15	40		
	5	100	-	
Clear Pulse Width, twL	10	50	-	ns
	15	40		
	5	0	_	
Clear Removal Time, tREM	10	0	-	ns
	15	0		

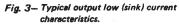
82 80 j 50 60 70 a٨ 1 72 70 60 50 40-69 - 77 (1.753 - 1.955) 16 30-20 6 7 2 1Ò 3 hr n _ 4~10 (0.102-0.254) 79-87 9205-29835



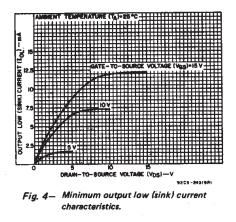
Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch) .

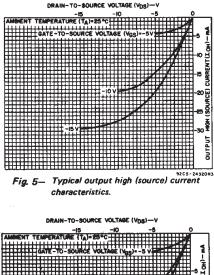
The photographs and dimensions of each CMOS chip The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of each of the the factor of the chip face tolerance. of -3 mils to +16 mils applicable to the nominal dimensions shown.

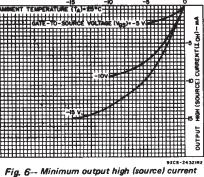












characteristics.

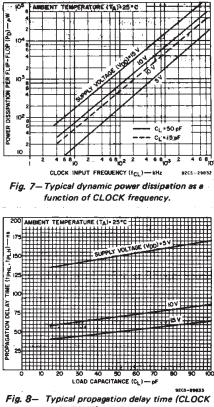
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CD40174B Types

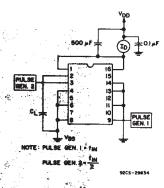
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STATIC ELECTRICAL CHARACTERISTICS

CHARAC-	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)					U N			
TERISTIC	Vo	VIN	V _{DD}				r ser i	+25			j'	
	(V)	(V);	.(V)-	-55	40	+85	+125	Min.	Тур.	Max.	s	1 ·
Quiescent Device	_	0,5	5	1	1	30	30	-	0.02	1	μΑ	1
	· _	0,10	10	2	2	60	60	_	0.02	2		t
Current, fDD		0,15	15	4	4	120	120	-	0.02	4		
Max.	$\frac{1}{2}$	0,20	20	20	20	600	600	-	0.04	20]	[
Output Low (Sink)	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	- 1	-]
Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-]	
I _{OL} Min.	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8		•	
Output High	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1			
(Source)	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-		
Current,	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6			
I _{OH} Min.	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	6.8			
Output Voltage:		0,5	5		-	.05			0	0.05		
Low-Level,		0,10	10		0	.05			3	0.05]	
V _{OL} Max.	. .	0,15	15	0.05			-	0	0.05			
Output Voltage:	— 1 a	0,5	5		4	.95		4.95	5	_	1	
High-Level,	-	0,10	10 ⁻		9	.95		9,95	10	- 1	1	
V _{OH} Min.	-	0,15	15		14.95			14.95	15	-		
Input Low	0.5,4.5	- -	5		1	.5		. –	_	1.5		1
Voltage,	1,9	-	10			3			-	3		
VIL Max.	1.5,13.5	—	15	4				-	-	4		
Input High Voltage, V _{IH} Min.	0.5,4.5	_	5.			3.5		3.5	-	.—] [
	1,9	-	10	7			7 *		-] [1 - 74	
	1.5,13.5	-	15			11		11	-	·		
Input Current [†] IN Max.	-	0,18	18	±0.1	±0.1	±1	±1	- :	±10 ⁻⁵	±0.1	ųА	



to OUTPUT) as a function of load capacitance.



9 . Dynamic power dissipation test circuit.

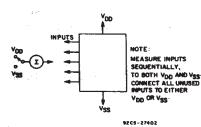
F, CL ĊL /nn CLOCK 10% H(HL) H(LH) DATA INPUT - 50% SULLIN" [†]SUGHL) - TLH -†THL ¥D0 - 90% OUTPUT -10% PHL TPLH TREM *(LH) OR (HL) OPTIONAL VDD CLEAR 50% 9203-2006984 0

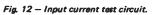
Fig. 10- Definition of setup, hold, propagation delay, and removal times.

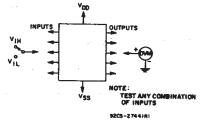
Fig. 11 - Quiescent device current test circuit.

CHARACTERISTIC	TEST CONDITIONS	LIMITS			UNITS	
	V _{DD} (V)	Min.	Min. Typ.			
Propagation Delay Time Clock to Output, tpHL, tpLH	5 10 15	 	150 70 50	300 140 100	ns ,	
Clear to Output, tpHL	5 10 15	-	100 50 40	200 100 80	ns	
Transition Time, ^t THL ^{, t} TLH	5 10 15		100 50 40	200 100 80	ns	
Minimum Pulse Width, Clock, ^t WL, ^t WH	5 10 15	-	65 30 20	130 60 40	ns	
Clear, t _{WL}	5 10 15		50 25 20	100 50 40	ns	
Minimum Data Setup Time, t _{SU}	5 10 15		20 10 0	40 20 10	ns	
Minimum Data Hold Time, t _H	5 10 15	-	40 20 15	80 40 30	ns	
Maximum Clock Frequency, f _{CL}	5 10 15	3.5 6 8	7 12 16		MHz	
Maximum Clock Rise or Fall Time, t _r CL, t _f CL	5 10 15	15 15 15	<u>;</u>	- - -	μs	
Input Capacitance, C _{IN} Clear		_	25	40	pF	
All other	-	-	5	7.5		
Minimum Clear Removal Time, ^t REM	5 10 15		40 15 10	0	ns	

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 k Ω



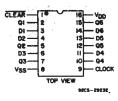






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Fig. 13 - Input voltage test circuit.

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